

**Silicon NPN Power Transistors**

**2SC2122**

**DESCRIPTION**

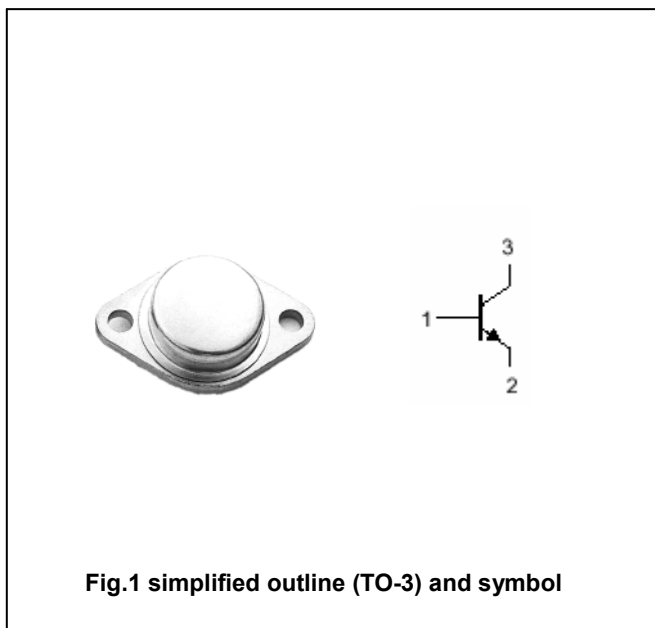
- With TO-3 package
- Short switching times.
- High dielectric strength.

**APPLICATIONS**

- For use in TV horizontal deflection stage

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Fig.1 simplified outline (TO-3) and symbol**

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	800	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	325	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		10	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25□	50	W
T <sub>j</sub>	Junction temperature		175	□
T <sub>stg</sub>	Storage temperature		-55~175	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =0;	325			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0;	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2.5 A			3.3	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =2.5 A			2.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			1.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2.5A ; V <sub>CE</sub> =10V	15			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		6		MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions